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	Department of Commerce at and Trademark Office	APPLICANT SUDA et	APPLICANT SUDA et al.					
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		U.S. P	atent Documents					
Examiner Initial	DOCUMENT NUMBER	DATE	Name	Class	SUB CLASS	FILING DATE		
		Forei	gn Patent Documents					
Examiner	DOCUMENT NUMBER	FILING DAT	E COUNTRY	CLASS	SUB	TRANSLATION		
Initial /MS/	09-181355	12/25/95	Japan		CLASS	Yes Abstract	No X	
/MS/	11-145514	11/5/97				Abstract	Х	
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	Other Do	ocuments (Incl	uding Author, Title, Date P	ertinent Par	es. Etc.)	<u> </u>		
			plication Serial No. PCT/JP					
/MS/	Norio Onojima et al., "Molecular-Beam Epitaxial Growth of Insulating AIN on Surface-Controlled SiC Substrate by HCI Gas Etching", Applied Physics Letters, Volume 80, Number 1 (7 January 200 76-78.							
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	nitial if citation is considere t in conformance and not co							

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